## Patent Claims

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- An optoelectronic module, comprising:
- a carrier element having electrical connection electrodes and electrical lines,
- at least one semiconductor component for emitting or detecting electromagnetic radiation, said semiconductor component being applied on the carrier element and being electrically connected
- to connection electrodes of the carrier element and having a radiation coupling area, and
  - at least one optical device assigned to the semiconductor component,

characterized in that

- a connecting layer made of a radiation-transmissive, deformable material is arranged in a gap between the radiation coupling area and the optical device, the optical device and the semiconductor component being fixed relative to one another in such a way that they
- are pressed against one another and that the connecting layer is thereby squeezed in such a way that it generates a force that strives to press the optical device and the radiation coupling area apart.
- 25 2. The optoelectronic module of claim 1, characterized in that the connecting layer has a thickness of at least 30 µm, preferably of at least 100 µm.
- 30 3. The optoelectronic module of claim 2, characterized in that the connecting layer has a thickness of greater than or equal to 150  $\mu$ m and less than or equal to 350  $\mu$ m.
  - 4. The optoelectronic module of one of the preceding claims, characterized

in that the connecting layer has a lacquer, preferably a circuit board lacquer, which is deformable in a cured state.

5 5. The optoelectronic module of one of the preceding claims,

characterized

in that a surface of the carrier element is at least partly coated for protection against external

- 10 influences with a material that is also contained in the connecting layer.
  - 6. The optoelectronic module of one of the preceding claims,
- 15 characterized

in that a refractive index of the connecting layer is adapted to a refractive index of a material of the semiconductor component that adjoins the connecting layer and/or to a refractive index of a material of the

- 20 optical device that adjoins the connecting layer.
  - 7. The optoelectronic module of one of the preceding claims,

characterized

- 25 in that the optical device has refractive and/or reflective elements.
  - 8. The optoelectronic module of one of the preceding claims,
- 30 characterized

in that the semiconductor component is a luminescence diode component.

9. The optoelectronic module of one of the preceding 35 claims,

characterized

in that the semiconductor component is a surfacemountable component.

- 10. A method for producing an optoelectronic module having at least the method steps of:
- providing

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- 5 a carrier element having electrical connection electrodes and electrical lines,
  - a semiconductor component for emitting or detecting electromagnetic radiation, said semiconductor component having a radiation coupling area, and
  - an optical device,
  - applying the semiconductor component on the carrier element and electrically connecting the semiconductor component to the connection electrodes, and
  - mounting the optical device above the radiation coupling area of the semiconductor component,

## characterized

- in that, prior to mounting the optical device, a curable and in a cured state radiation-transmissive and deformable composition is applied at least over the radiation coupling area of the semiconductor component,
- in that the applied composition is at least partly cured or let to be cured, and
  - in that the optical device and the semiconductor component are fixed relative to one another in such a way that they are pressed against one another and thereby that the connecting layer is squeezed in such a way that it generates a force the composition strives to press the optical device and the radiation coupling area apart.
  - 11. The method of claim 10,
- 35 characterized

in that the composition is applied in the form of a layer having a thickness of at least 30  $\mu m,$  preferably of at least 100  $\mu m.$ 

12. The method of claim 11, characterized

in that the composition is applied in the form of a layer having a thickness of greater than or equal to 150 µm and less than or equal to 350 µm.

- 13. The method of one of claims 10 to 12, characterized
- 10 in that the composition has a lacquer, preferably a circuit board lacquer, which is deformable in a cured state.
  - 14. The method of one of claims 10 to 13,
- in that the composition is applied at least to a part of a surface of the carrier element for protection against external influences.
- 20 15. The method of claim 14, characterized in that the composition is applied to the radiation coupling area and to the surface of the carrier element in a single method step.